

RF LDMOS Wideband Integrated Power Amplifiers

The MD7IC21100N wideband integrated circuit is designed with on-chip matching that makes it usable from 2110 to 2170 MHz. This multi-stage structure is rated for 24 to 32 Volt operation and covers all typical cellular base station modulation formats including TD-SCDMA.

- Typical Single-Carrier W-CDMA Performance: $V_{DD} = 28$ Volts, $I_{DQ1A} + I_{DQ1B} = 190$ mA, $I_{DQ2A} + I_{DQ2B} = 925$ mA, $P_{out} = 32$ Watts Avg., $f = 2167.5$ MHz, IQ Magnitude Clipping, Channel Bandwidth = 3.84 MHz, Input Signal PAR = 7.5 dB @ 0.01% Probability on CCDF.
Power Gain — 28.5 dB
Power Added Efficiency — 30%
Device Output Signal PAR — 6.1 dB @ 0.01% Probability on CCDF
ACPR @ 5 MHz Offset — -38 dBc in 3.84 MHz Channel Bandwidth
- Capable of Handling 5:1 VSWR, @ 32 Vdc, 2140 MHz, $P_{out} = 110$ Watts CW (3 dB Input Overdrive from Rated P_{out})
- Stable into a 5:1 VSWR. All Spurs Below -60 dBc @ 1 mW to 100 Watts CW P_{out} .
- Typical P_{out} @ 1 dB Compression Point ≈ 110 Watts CW

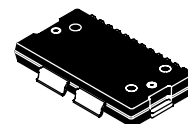
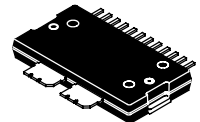
Features

- 100% PAR Tested for Guaranteed Output Power Capability
- Characterized with Series Equivalent Large-Signal Impedance Parameters and Common Source S-Parameters
- On-Chip Matching (50 Ohm Input, on a per side basis, DC Blocked)
- Internally Matched for Ease of Use
- Integrated Quiescent Current Temperature Compensation with Enable/Disable Function ⁽¹⁾
- Integrated ESD Protection
- 225°C Capable Plastic Package
- In Tape and Reel. R1 Suffix = 500 Units, 44 mm Tape Width, 13 inch Reel.

MD7IC21100NR1
MD7IC21100GNR1
MD7IC21100NBR1

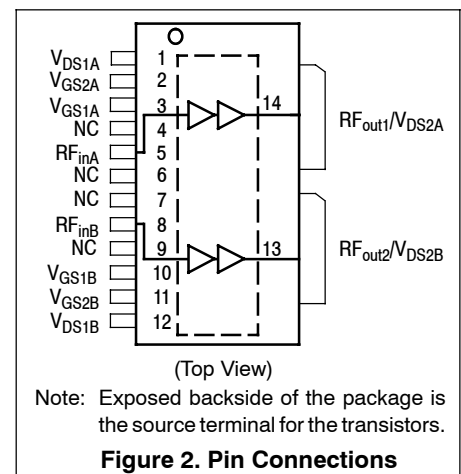
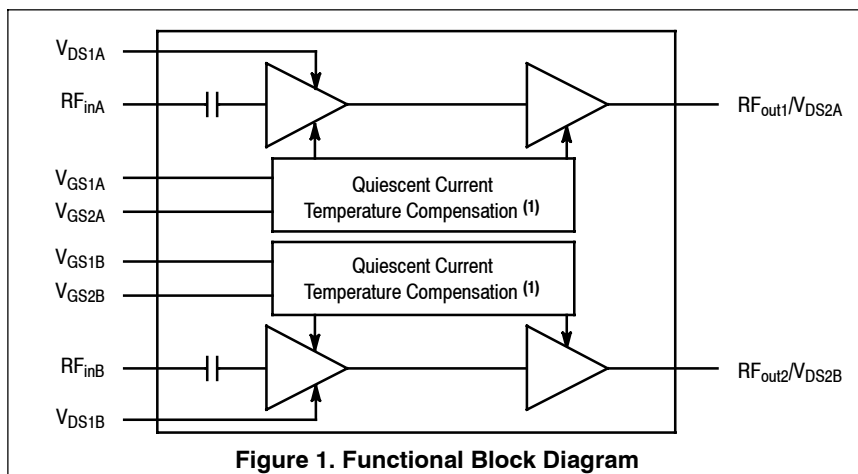
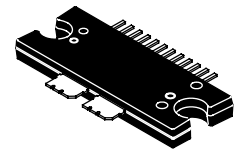
2110-2170 MHz, 32 W AVG., 28 V
SINGLE W-CDMA
RF LDMOS WIDEBAND
INTEGRATED POWER AMPLIFIERS

CASE 1618-02
TO-270 WB-14
PLASTIC
MD7IC21100NR1



CASE 1621-02
TO-270 WB-14 GULL
PLASTIC
MD7IC21100GNR1

CASE 1617-02
TO-272 WB-14
PLASTIC
MD7IC21100NBR1



1. Refer to AN1977, *Quiescent Current Thermal Tracking Circuit in the RF Integrated Circuit Family* and to AN1987, *Quiescent Current Control for the RF Integrated Circuit Device Family*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1977 or AN1987.

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain–Source Voltage	V_{DS}	–0.5, +65	Vdc
Gate–Source Voltage	V_{GS}	–0.5, +6.0	Vdc
Operating Voltage	V_{DD}	32, +0	Vdc
Storage Temperature Range	T_{stg}	–65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature ^(1,2)	T_J	225	°C
Input Power	P_{in}	29	dBm

Table 2. Thermal Characteristics

Characteristic	Symbol	Value ^(2,3)	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$		°C/W
(Case Temperature 76°C, 32 W CW) Stage 1, 28 Vdc, $I_{DQ1A} + I_{DQ1B} = 190$ mA		2.7	
(Case Temperature 76°C, 32 W CW) Stage 2, 28 Vdc, $I_{DQ2A} + I_{DQ2B} = 925$ mA		0.7	

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	0
Machine Model (per EIA/JESD22-A115)	A
Charge Device Model (per JESD22-C101)	III

Table 4. Moisture Sensitivity Level

Test Methodology	Rating	Package Peak Temperature	Unit
Per JESD22-A113, IPC/JEDEC J-STD-020	3	260	°C

Table 5. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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Stage 1 — Off Characteristics ⁽⁴⁾

Zero Gate Voltage Drain Leakage Current ($V_{DS} = 65$ Vdc, $V_{GS} = 0$ Vdc)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28$ Vdc, $V_{GS} = 0$ Vdc)	I_{DSS}	—	—	1	μAdc
Gate–Source Leakage Current ($V_{GS} = 1.5$ Vdc, $V_{DS} = 0$ Vdc)	I_{GSS}	—	—	1	μAdc

Stage 1 — On Characteristics ⁽⁴⁾

Gate Threshold Voltage ($V_{DS} = 10$ Vdc, $I_D = 50$ μAdc)	$V_{GS(th)}$	1	2	3	Vdc
Gate Quiescent Voltage ($V_{DS} = 28$ Vdc, $I_{DQ1A} + I_{DQ1B} = 190$ mAdc)	$V_{GS(Q)}$	—	2.9	—	Vdc
Fixture Gate Quiescent Voltage ($V_{DD} = 28$ Vdc, $I_{DQ1A} + I_{DQ1B} = 190$ mAdc, Measured in Functional Test)	$V_{GG(Q)}$	5.5	6.3	7	Vdc

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes – AN1955.
4. Each side of device measured separately.

(continued)

Table 5. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
Stage 2 — Off Characteristics ⁽¹⁾					
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 65\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 1.5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc
Stage 2 — On Characteristics ⁽¹⁾					
Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 270\text{ }\mu\text{Adc}$)	$V_{GS(th)}$	1	2	3	Vdc
Gate Quiescent Voltage ($V_{DS} = 28\text{ Vdc}$, $I_{DQ2A} + I_{DQ2B} = 925\text{ mAdc}$)	$V_{GS(Q)}$	—	2.8	—	Vdc
Fixture Gate Quiescent Voltage ($V_{DD} = 28\text{ Vdc}$, $I_{DQ2A} + I_{DQ2B} = 925\text{ mAdc}$, Measured in Functional Test)	$V_{GG(Q)}$	5.3	5.9	6.8	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 1\text{ Adc}$)	$V_{DS(on)}$	0.1	0.3	0.8	Vdc
Stage 2 — Dynamic Characteristics ^(1,2)					
Output Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{oss}	—	380	—	pF
Functional Tests ⁽³⁾ (In Freescale Wideband 2110–2170 MHz Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ1A} + I_{DQ1B} = 190\text{ mA}$, $I_{DQ2A} + I_{DQ2B} = 925\text{ mA}$, $P_{out} = 32\text{ W Avg.}$, $f = 2167.5\text{ MHz}$, Single-Carrier W-CDMA, IQ Magnitude Clipping, Input Signal PAR = 7.5 dB @ 0.01% Probability on CCDF. ACPR measured in 3.84 MHz Channel Bandwidth @ $\pm 5\text{ MHz}$ Offset.					
Power Gain	G_{ps}	27	28.5	32	dB
Power Added Efficiency	PAE	27	30	—	%
Output Peak-to-Average Ratio @ 0.01% Probability on CCDF	PAR	5.6	6.1	—	dB
Adjacent Channel Power Ratio	ACPR	—	-38	-36	dBc
Input Return Loss	IRL	—	-15	-9	dB
Typical Performances ⁽³⁾ (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ1A} + I_{DQ1B} = 190\text{ mA}$, $I_{DQ2A} + I_{DQ2B} = 925\text{ mA}$, 2110–2170 MHz Bandwidth					
P_{out} @ 1 dB Compression Point, CW	P_{1dB}	—	110	—	W
IMD Symmetry @ 112 W PEP, P_{out} where IMD Third Order Intermodulation $\cong 30\text{ dBc}$ (Delta IMD Third Order Intermodulation between Upper and Lower Sidebands > 2 dB)	IMD_{sym}	—	50	—	MHz
VBW Resonance Point (IMD Third Order Intermodulation Inflection Point)	VBW_{res}	—	50	—	MHz
Gain Flatness in 60 MHz Bandwidth @ $P_{out} = 32\text{ W Avg.}$	G_F	—	0.3	—	dB
Quiescent Current Accuracy over Temperature with 4.7 k Ω Gate Feed Resistors (-30 to 85°C) ⁽⁴⁾	ΔI_{QT}	—	± 3	—	%
Average Deviation from Linear Phase in 60 MHz Bandwidth @ $P_{out} = 110\text{ W CW}$	Φ	—	0.6	—	$^\circ$
Average Group Delay @ $P_{out} = 110\text{ W CW}$, $f = 2140\text{ MHz}$	Delay	—	2.6	—	ns
Part-to-Part Insertion Phase Variation @ $P_{out} = 110\text{ W CW}$, $f = 2140\text{ MHz}$, Six Sigma Window	$\Delta\Phi$	—	35	—	$^\circ$
Gain Variation over Temperature (-30°C to $+85^\circ\text{C}$)	ΔG	—	0.042	—	dB/ $^\circ\text{C}$
Output Power Variation over Temperature (-30°C to $+85^\circ\text{C}$)	ΔP_{1dB}	—	0.003	—	dB/ $^\circ\text{C}$

1. Each side of device measured separately.

2. Part internally matched both on input and output.

3. Measurement made with device in a single-ended configuration.

4. Refer to AN1977, *Quiescent Current Thermal Tracking Circuit in the RF Integrated Circuit Family* and to AN1987, *Quiescent Current Control for the RF Integrated Circuit Device Family*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes – AN1977 or AN1987.

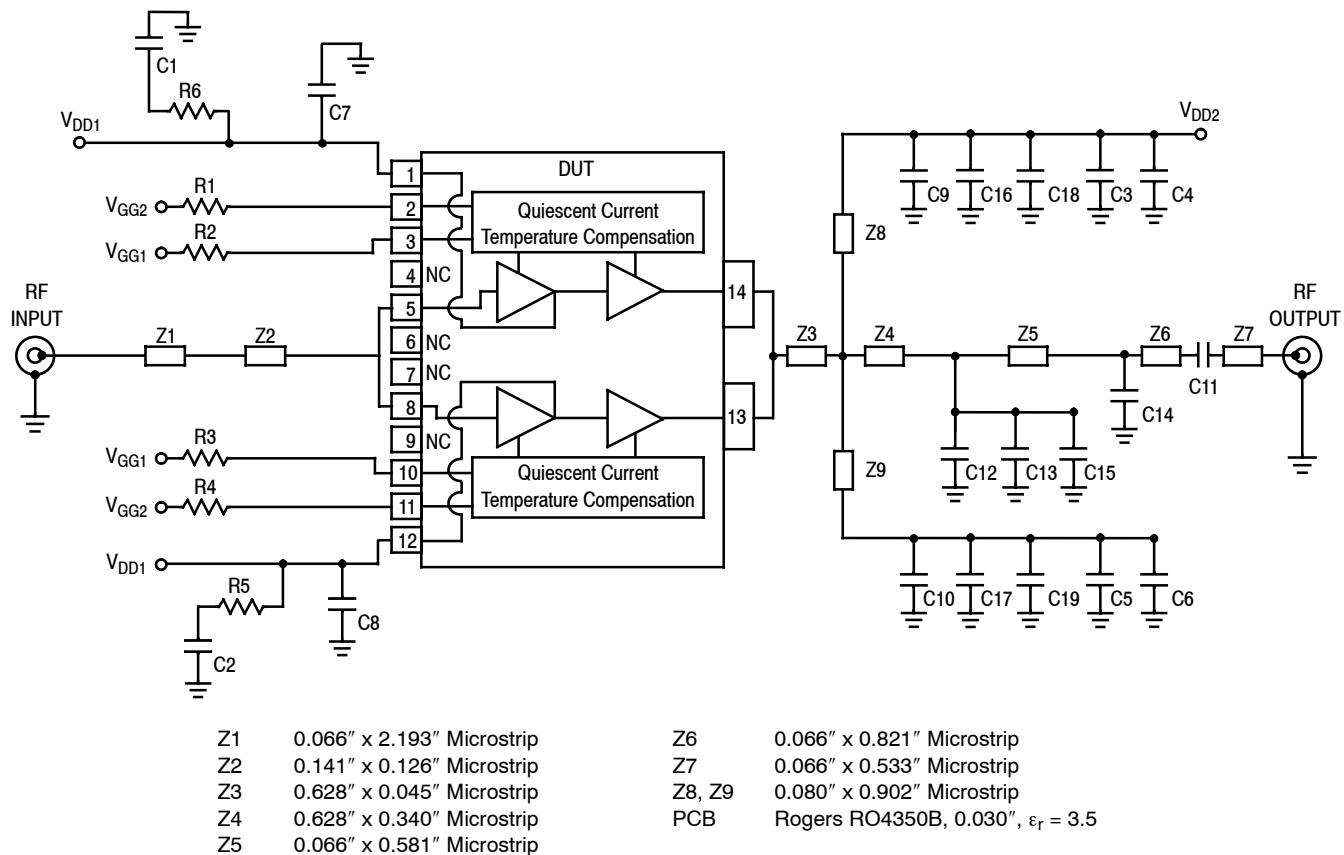


Figure 3. MD7IC21100NR1(GNR1)(NBR1) Test Circuit Schematic

Table 6. MW7IC2220NR1(GNR1)(NBR1) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
C1, C2, C3, C4, C5, C6	10 μ F, 50 V Chip Capacitors	GRM55DR61H106KA88B	Murata
C7, C8, C9, C10	5.1 pF Chip Capacitors	ATC100B5R1CT500XT	ATC
C11	10 pF Chip Capacitor	ATC100B100JT500XT	ATC
C12, C13, C14	1.2 pF Chip Capacitors	ATC100B1R2CT500XT	ATC
C15	0.5 pF Chip Capacitor	ATC100B0R5CT500XT	ATC
C16, C17	0.1 μ F, 100 V Chip Capacitors	GRM32NR72A104KA01B	Murata
C18, C19	1 μ F, 100 V Chip Capacitors	GRM32EER72A105KA01L	Murata
R1, R2, R3, R4	4.7 k Ω , 1/4 W Chip Resistors	CRCW12064701FKEA	Vishay
R5, R6	2 Ω , 1/2 W Chip Resistors	CRCW12102R00FKEA	Vishay

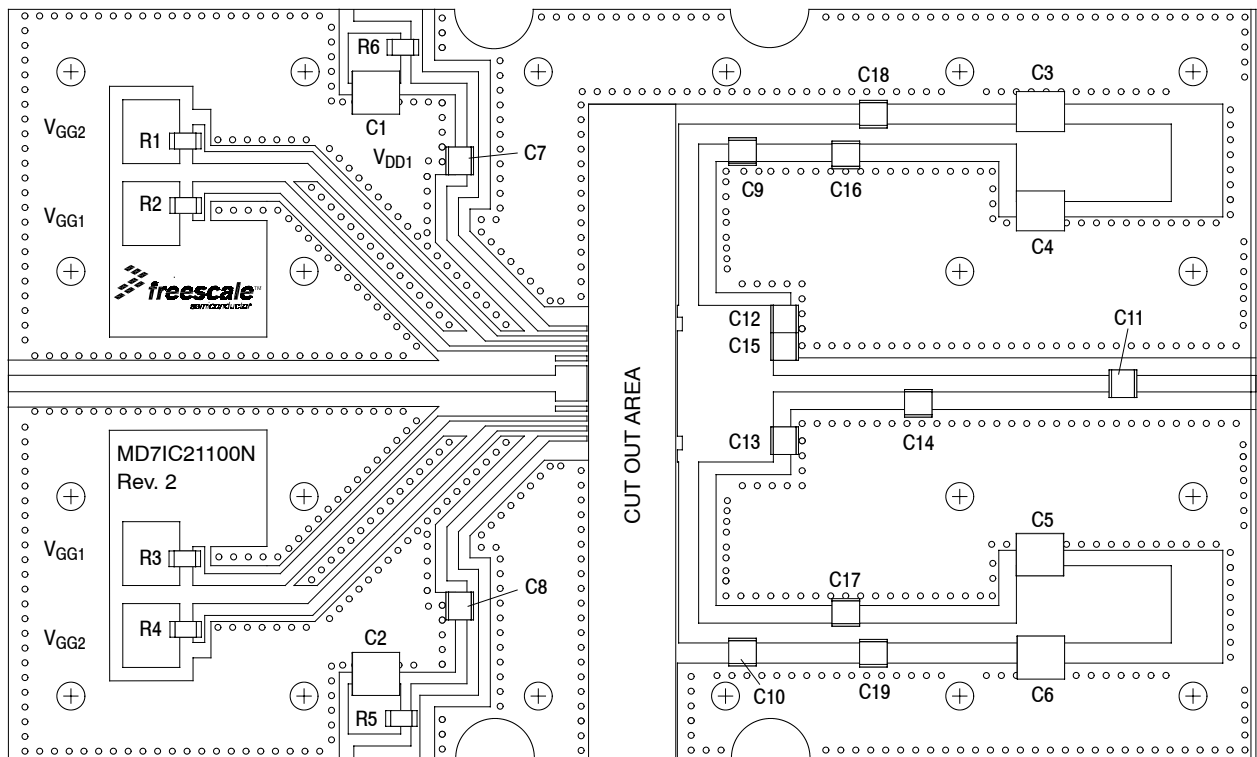


Figure 4. MD7IC21100NR1(GNR1)(NBR1) Test Circuit Component Layout

TYPICAL CHARACTERISTICS

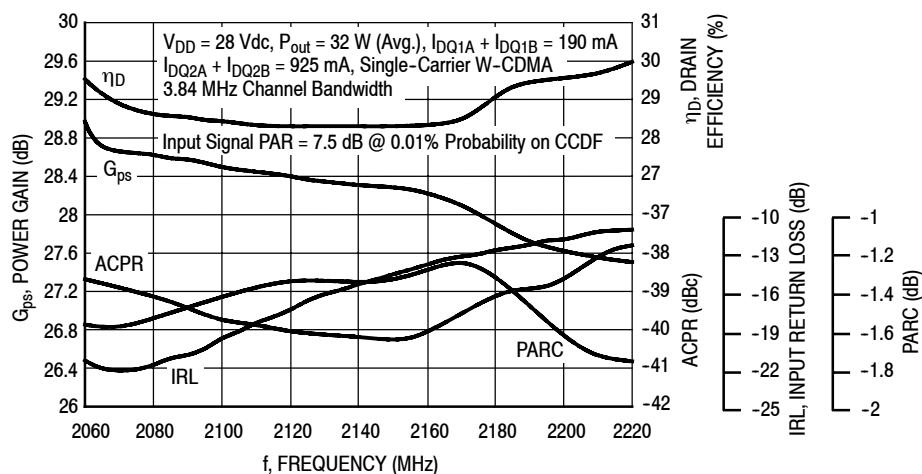


Figure 5. Output Peak-to-Average Ratio Compression (PARC) versus Broadband Performance @ $P_{out} = 32$ Watts Avg.

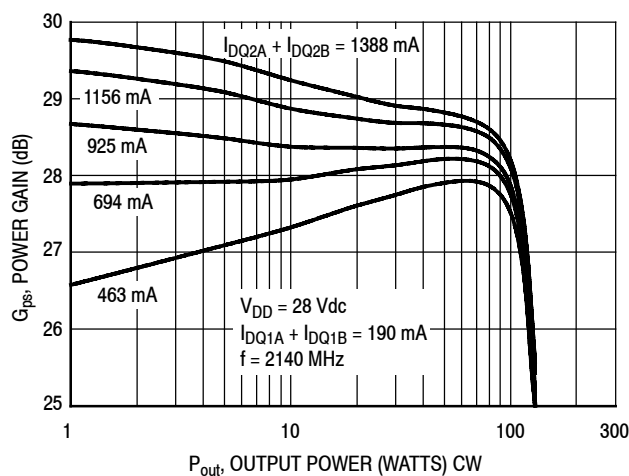


Figure 6. Power Gain versus Output Power @ $I_{DQ1A} + I_{DQ1B} = 190 \text{ mA}$

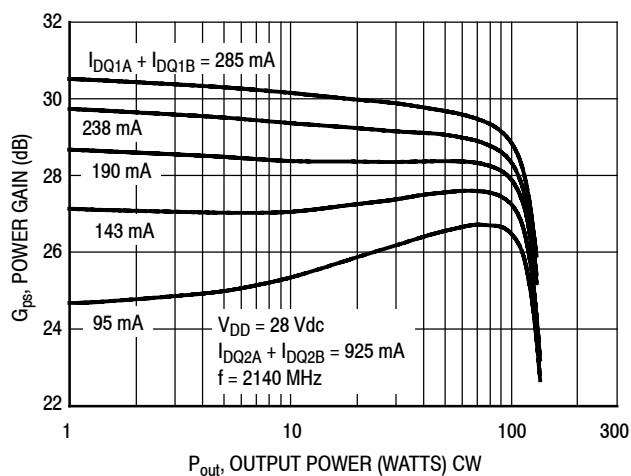


Figure 7. Power Gain versus Output Power @ $I_{DQ2A} + I_{DQ2B} = 925 \text{ mA}$

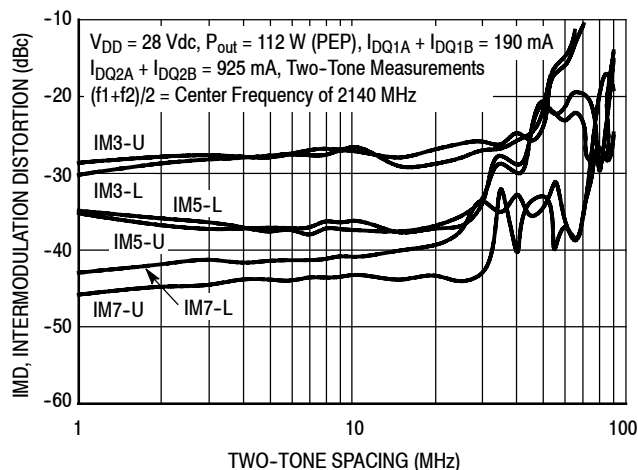


Figure 8. Intermodulation Distortion Products versus Tone Spacing

TYPICAL CHARACTERISTICS

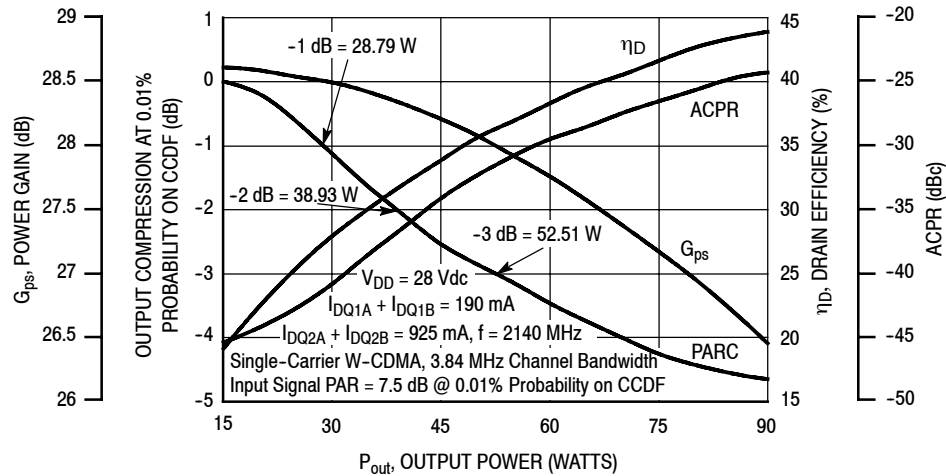


Figure 9. Output Peak-to-Average Ratio Compression (PARC) versus Output Power

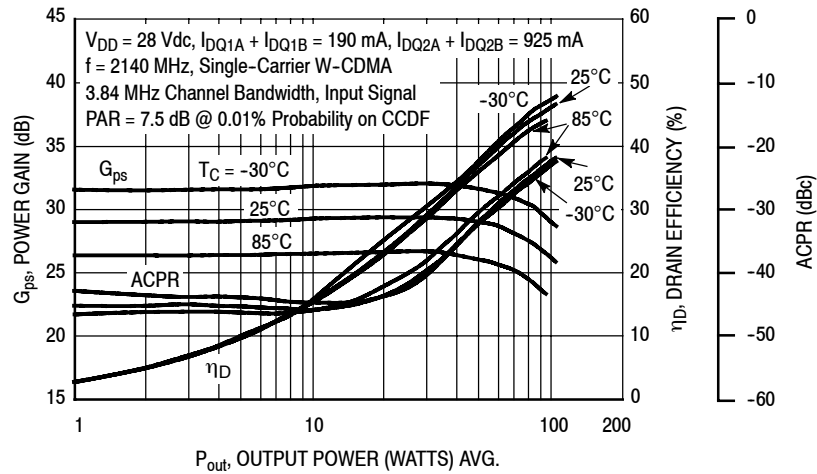


Figure 10. Single-Carrier W-CDMA Power Gain, Drain Efficiency and ACPR versus Output Power

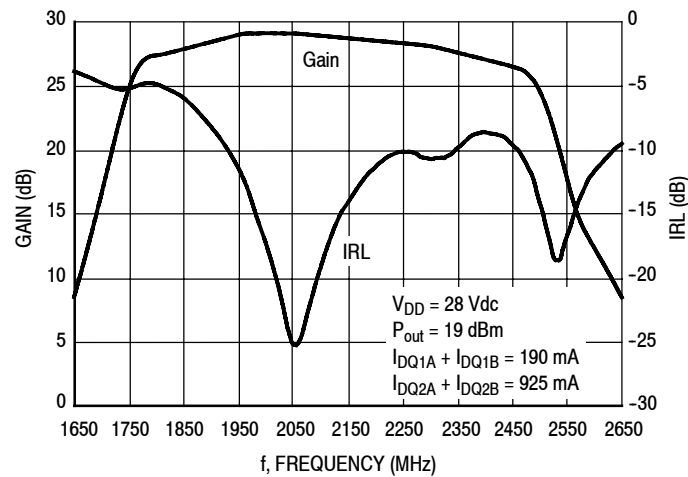


Figure 11. Broadband Frequency Response

W-CDMA TEST SIGNAL

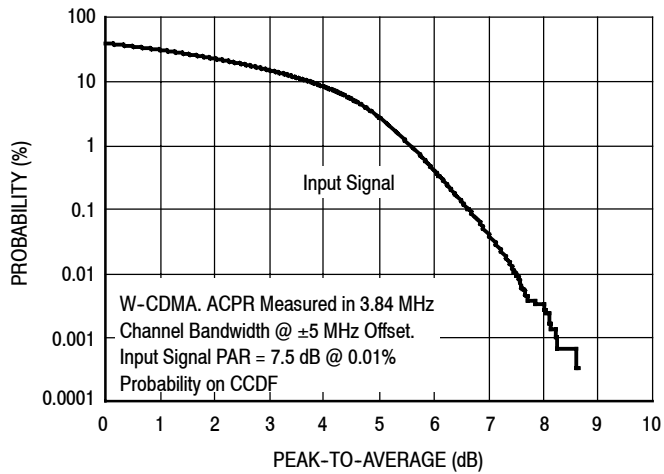


Figure 12. CCDF W-CDMA IQ Magnitude Clipping, Single-Carrier Test Signal

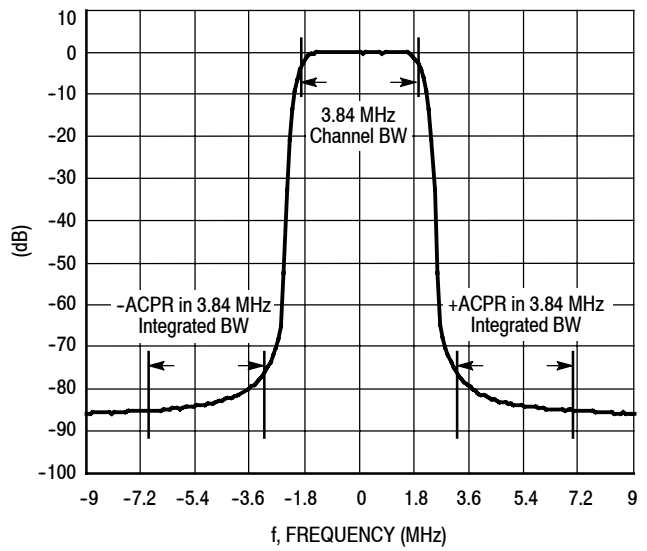
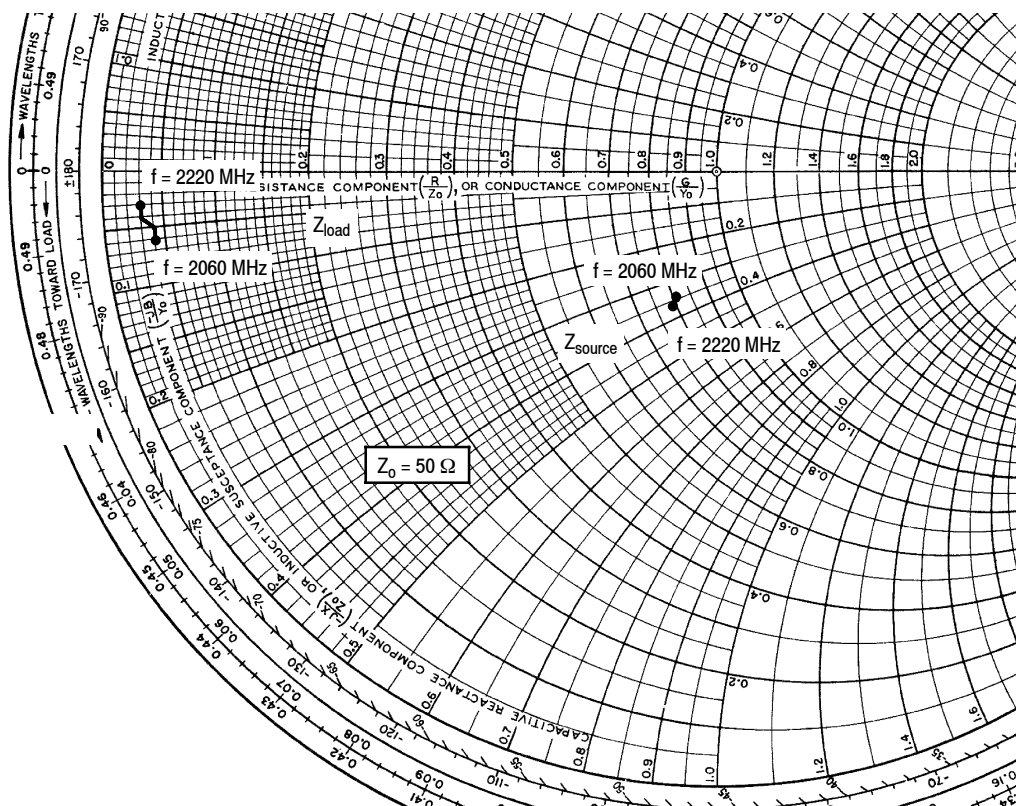


Figure 13. Single-Carrier W-CDMA Spectrum



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ1A} + I_{DQ1B} = 190 \text{ mA}$, $I_{DQ2A} + I_{DQ2B} = 925 \text{ mA}$, $P_{out} = 32 \text{ W Avg.}$

f MHz	$Z_{source}^{(1)}$ Ω	Z_{load} Ω
2060	$40.60 - j16.80$	$1.99 - j2.90$
2080	$40.51 - j16.95$	$1.90 - j2.74$
2100	$40.42 - j17.10$	$1.82 - j2.58$
2120	$40.32 - j17.26$	$1.75 - j2.41$
2140	$40.21 - j17.42$	$1.68 - j2.24$
2160	$40.10 - j17.58$	$1.62 - j2.08$
2180	$39.97 - j17.75$	$1.55 - j1.92$
2200	$39.84 - j17.91$	$1.48 - j1.77$
2220	$39.70 - j18.08$	$1.41 - j1.60$

(1) Both 50Ω inputs in parallel as per the product test fixture.

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

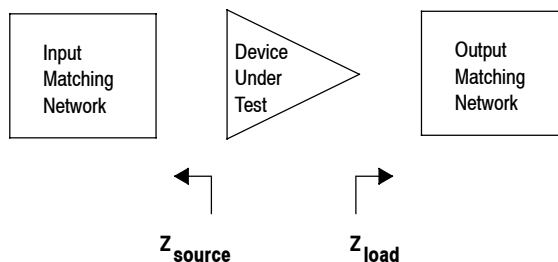
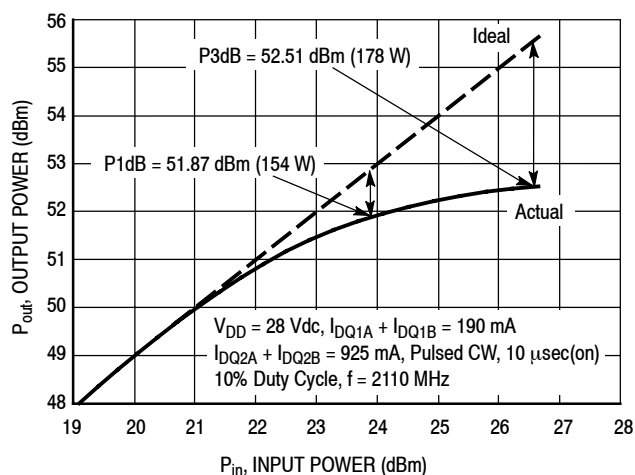


Figure 14. Series Equivalent Source and Load Impedance

ALTERNATIVE PEAK TUNE LOAD PULL CHARACTERISTICS

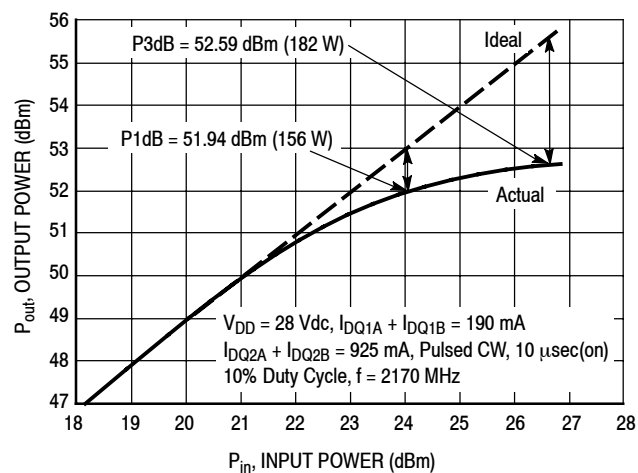


NOTE: Load Pull Test Fixture Tuned for Peak P1dB Output Power @ 28 V

Test Impedances per Compression Level

	Z_{source} Ω	Z_{load} Ω
P1dB	48.64 - j0.94	1.02 - j3.36

Figure 15. Pulsed CW Output Power versus Input Power @ 28 V @ 2110 MHz



NOTE: Load Pull Test Fixture Tuned for Peak P1dB Output Power @ 28 V

Test Impedances per Compression Level

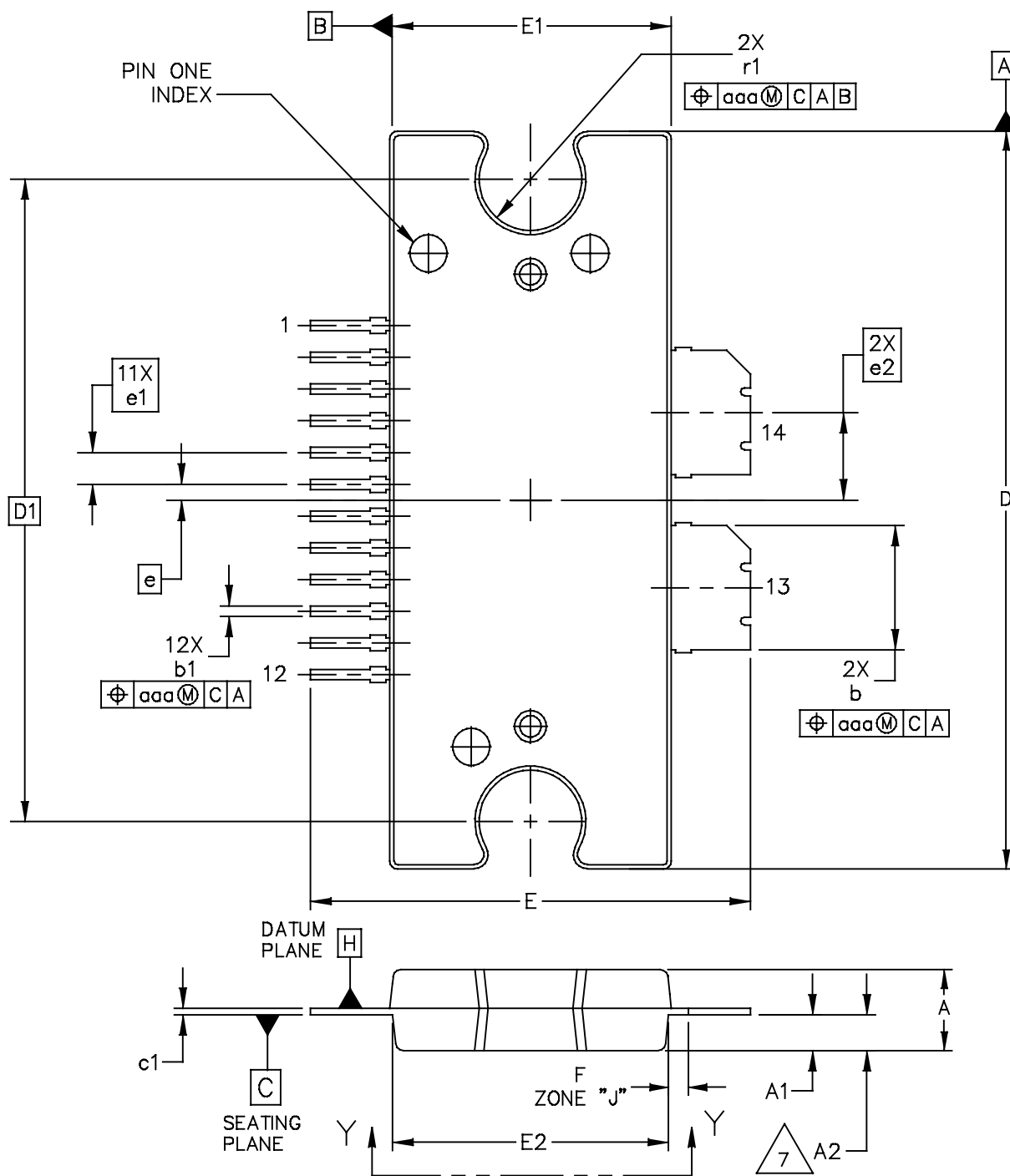
	Z_{source} Ω	Z_{load} Ω
P1dB	51.04 + j0.32	0.92 - j3.48

Figure 16. Pulsed CW Output Power versus Input Power @ 28 V @ 2170 MHz

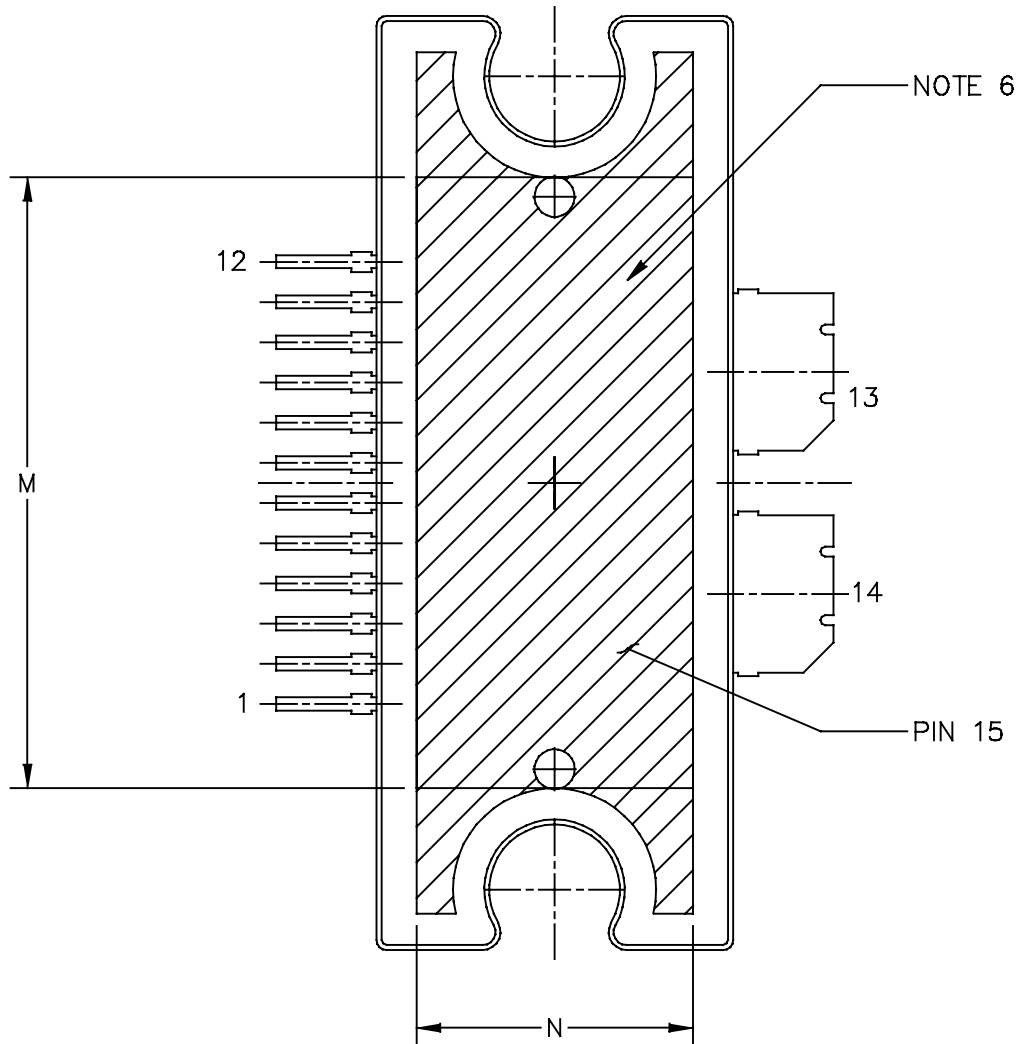
Table 7. Common Source S-Parameters ($V_{DD} = 28\text{ V}$, $I_{DQ1A} + I_{DQ1B} = 190\text{ mA}$, $I_{DQ2A} + I_{DQ2B} = 925\text{ mA}$, $T_A = 25^\circ\text{C}$, 50 Ohm System)

f MHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠ φ	S ₂₁	∠ φ	S ₁₂	∠ φ	S ₂₂	∠ φ
1700	0.652	137.6	2.264	127.9	0.000338	110.1	0.986	170.7
1750	0.584	141.8	6.373	105.7	0.00176	-161.5	0.962	166.0
1800	0.967	149.5	22.975	30.1	0.00809	148.5	0.633	163.7
1850	0.830	109.6	14.760	-54.3	0.00544	88.8	0.872	-179.3
1900	0.609	93.0	12.528	-81.7	0.00445	92.7	0.891	175.2
1950	0.376	73.2	12.727	-115.4	0.00571	97.8	0.848	172.6
2000	0.159	50.5	11.639	-142.6	0.00781	75.0	0.785	177.3
2050	0.093	-129.9	11.706	-174.5	0.00711	50.8	0.863	-178.8
2100	0.200	-148.4	10.735	159.4	0.00593	37.7	0.921	179.9
2150	0.304	-156.5	9.872	135.1	0.00461	28.3	0.950	177.7
2200	0.386	-169.3	8.929	113.7	0.00366	28.3	0.958	176.2
2250	0.432	178.3	8.421	94.5	0.00304	33.7	0.960	175.5
2300	0.459	163.6	8.238	75.8	0.00281	41.0	0.962	175.2
2350	0.406	145.8	9.041	52.8	0.00253	46.3	0.963	175.5
2400	0.334	134.7	8.312	21.8	0.00255	54.7	0.971	175.7
2450	0.238	120.3	7.167	-5.1	0.00262	60.5	0.977	175.8
2500	0.133	110.4	5.879	-28.8	0.00270	65.2	0.981	175.8
2550	0.020	149.0	4.788	-50.7	0.00304	66.7	0.982	175.8
2600	0.102	-116.2	3.837	-70.6	0.00319	68.5	0.982	175.7
2650	0.204	-121.9	3.053	-89.3	0.00356	67.3	0.982	175.5
2700	0.280	-129.7	2.415	-105.9	0.00369	66.9	0.981	175.2
2750	0.342	-135.1	1.931	-121.3	0.00397	66.4	0.981	174.7
2800	0.392	-138.0	1.551	-135.6	0.00446	67.5	0.979	174.0
2850	0.455	-140.7	1.231	-148.0	0.00466	57.7	0.980	173.3
2900	0.503	-145.9	1.016	-160.1	0.00445	52.3	0.980	172.6
2950	0.531	-147.9	0.831	-172.2	0.00434	53.4	0.980	171.8
3000	0.566	-148.9	0.677	176.6	0.00437	54.8	0.981	171.1
3050	0.601	-149.7	0.550	166.3	0.00453	56.6	0.982	170.4
3100	0.634	-150.5	0.449	156.9	0.00486	57.6	0.982	170.0

PACKAGE DIMENSIONS



© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED.	MECHANICAL OUTLINE	PRINT VERSION NOT TO SCALE	
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	CASE NUMBER: 1617-02		27 JUN 2007
	STANDARD: NON-JEDEC		



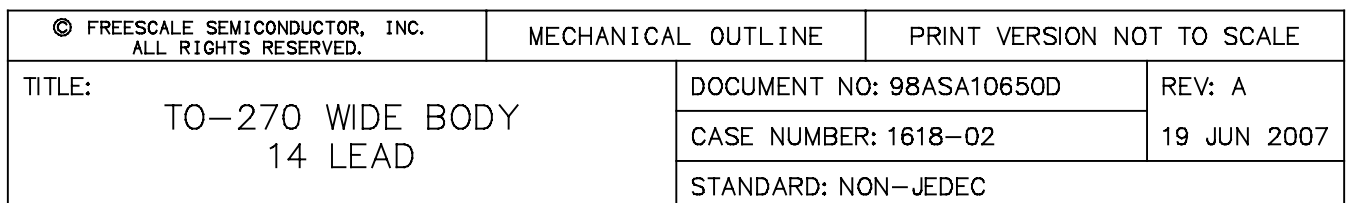
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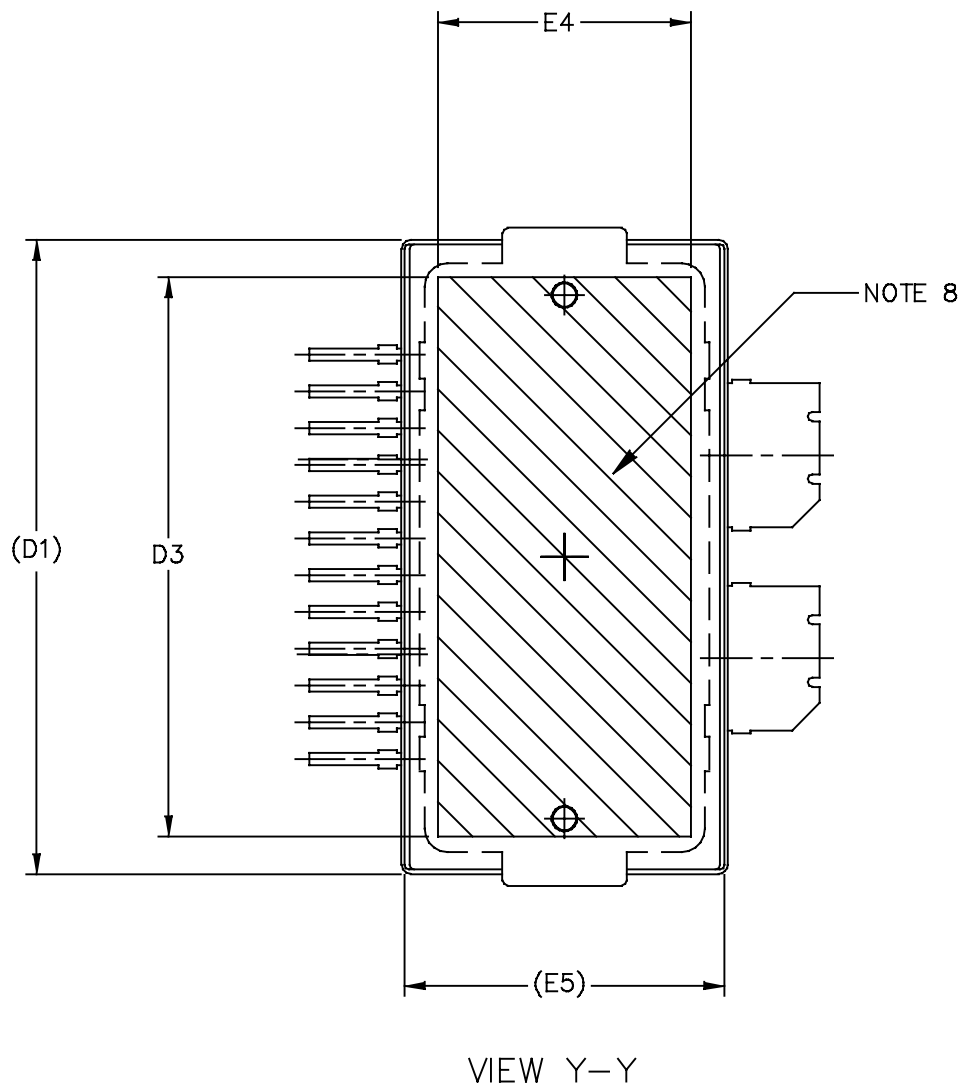
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		CASE NUMBER: 1617-02		27 JUN 2007	
		STANDARD: NON-JEDEC			

NOTES:

1. CONTROLLING DIMENSION: INCH
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
3. DATUM PLANE -H- IS LOCATED AT THE TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 (0.15) PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
5. DIMENSIONS "b" AND "b1" DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 (0.13) TOTAL IN EXCESS OF THE "b" AND "b1" DIMENSIONS AT MAXIMUM MATERIAL CONDITION.
6. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG.
7. DIM A2 APPLIES WITHIN ZONE "J" ONLY.

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	.100	.104	2.54	2.64	b	.154	.160	3.91	4.06
A1	.039	.043	0.99	1.09	b1	.010	.016	0.25	0.41
A2	.040	.042	1.02	1.07	c1	.007	.011	0.18	0.28
D	.928	.932	23.57	23.67	e	.020 BSC		0.51 BSC	
D1	.810 BSC		20.57 BSC		e1	.040 BSC		1.02 BSC	
E	.551	.559	14.00	14.20	e2	.1105 BSC		2.807 BSC	
E1	.353	.357	8.97	9.07	r1	.063	.068	1.6	1.73
E2	.346	.350	8.79	8.89					
F	.025 BSC		0.64 BSC		aaa	.004		0.10	
M	.600	----	15.24	----					
N	.270	----	6.86	----					
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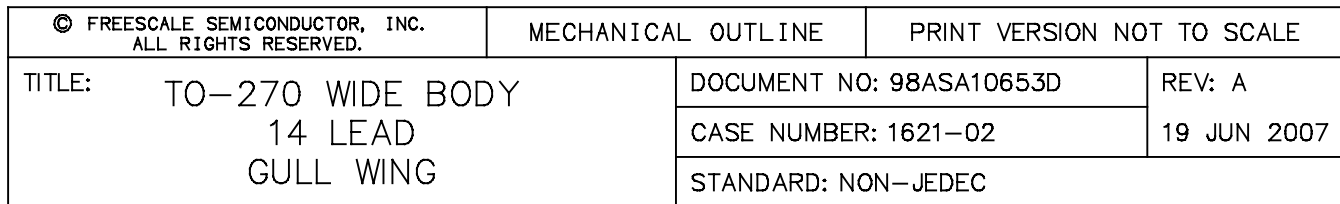


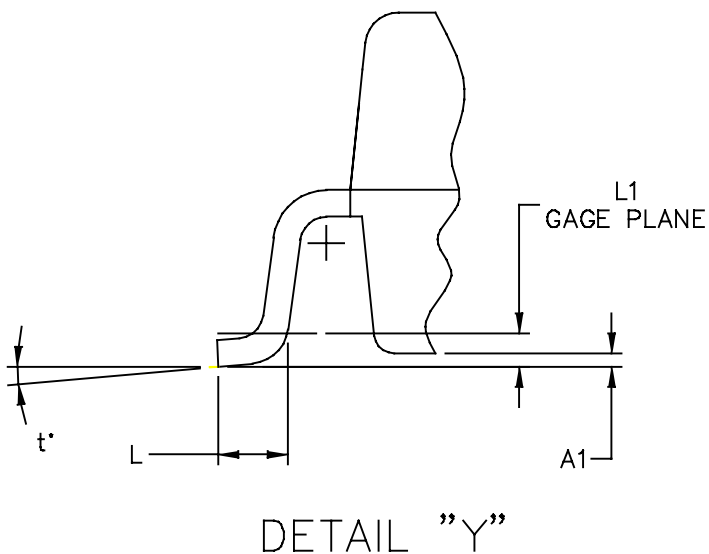
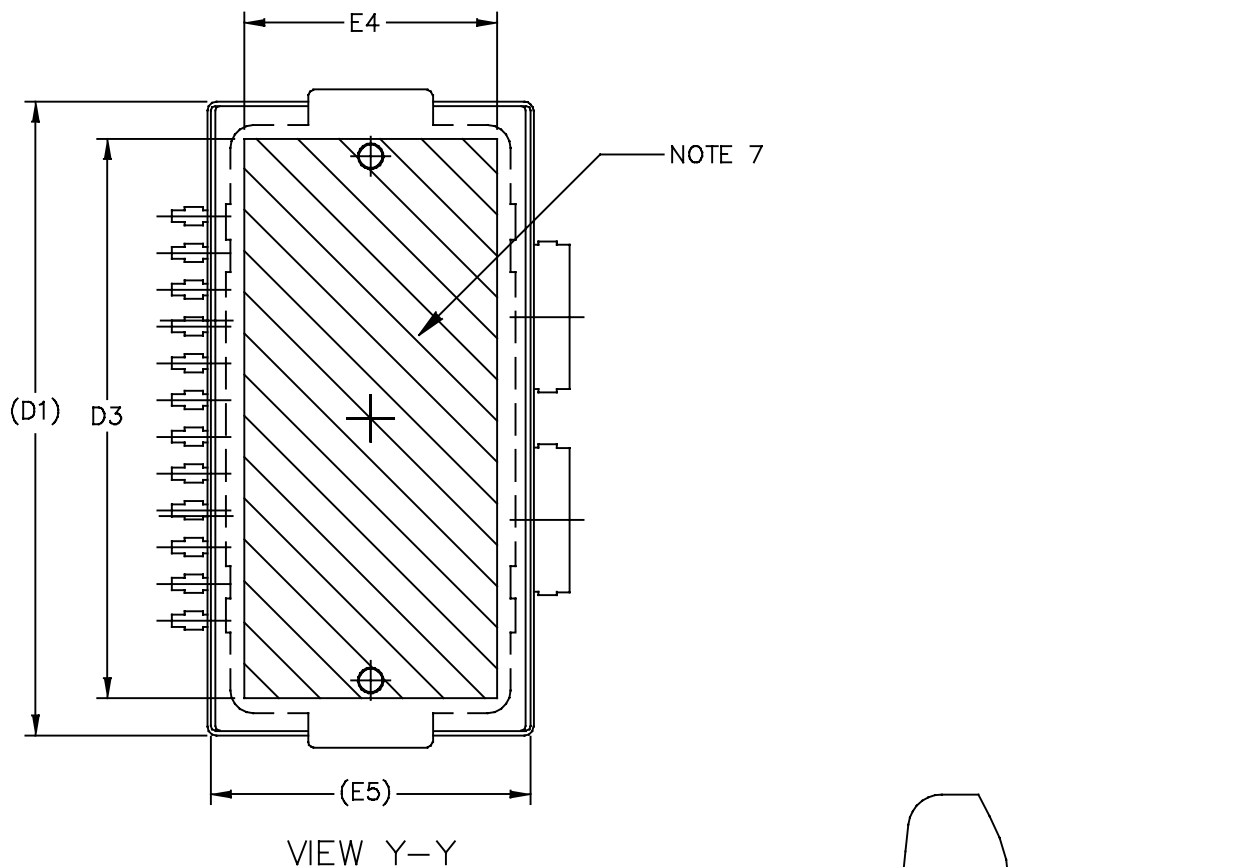
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			CASE NUMBER: 1618-02		19 JUN 2007
			STANDARD: NON-JEDEC		

NOTES:

1. CONTROLLING DIMENSION: INCH
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
3. DATUM PLANE -H- IS LOCATED AT THE TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
5. DIMENSIONS "b" AND "b1" DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 TOTAL IN EXCESS OF THE "b" AND "b1" DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. DATUMS -A- AND -B- TO BE DETERMINED AT DATUM PLANE -H-.
7. DIMENSION A2 APPLIES WITHIN ZONE "J" ONLY.
8. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG.

INCH		MILLIMETER		INCH		MILLIMETER	
DIM	MIN	MAX	MIN	MAX	DIM	MIN	MAX
A	.100	.104	2.54	2.64	F	.025 BSC	
A1	.039	.043	0.99	1.09	b	.154	.160
A2	.040	.042	1.02	1.07	b1	.010	.016
D	.712	.720	18.08	18.29	c1	.007	.011
D1	.688	.692	17.48	17.58	e	.020 BSC	
D2	.011	.019	0.28	0.48	e1	.040 BSC	
D3	.600	---	15.24	---	e2	.1105 BSC	
E	.551	.559	14	14.2	aaa	.004	.10
E1	.353	.357	8.97	9.07			
E2	.132	.140	3.35	3.56			
E3	.124	.132	3.15	3.35			
E4	.270	---	6.86	---			
E5	.346	.350	8.79	8.89			
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	CASE NUMBER: 1621-02			19 JUN 2007	
	STANDARD: NON-JEDEC				

MD7IC21100NR1 MD7IC21100GNR1 MD7IC21100NBR1

NOTES:

1. CONTROLLING DIMENSION: INCH
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
3. DATUM PLANE -H- IS LOCATED AT THE TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
5. DIMENSIONS "b" AND "b1" DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 TOTAL IN EXCESS OF THE "b" AND "b1" DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. DATUMS -A- AND -B- TO BE DETERMINED AT DATUM PLANE -H-.
7. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG.

INCH			MILLIMETER		INCH			MILLIMETER	
DIM	MIN	MAX	MIN	MAX	DIM	MIN	MAX	MIN	MAX
A	.100	.104	2.54	2.64	L	.018	.024	0.46	0.61
A1	.001	.004	0.02	0.10	L1	.010 BSC		0.25 BSC	
A2	.099	.110	2.51	2.79	b	.154	.160	3.91	4.06
D	.712	.720	18.08	18.29	b1	.010	.016	0.25	0.41
D1	.688	.692	17.48	17.58	c1	.007	.011	.18	.28
D2	.011	.019	0.28	0.48	e	.020 BSC		0.51 BSC	
D3	.600	---	15.24	---	e1	.040 BSC		1.02 BSC	
E	.429	.437	10.9	11.1	e2	.1105 BSC		2.807 BSC	
E1	.353	.357	8.97	9.07	t	2°	8°	2°	8°
E2	.132	.140	3.35	3.56	aaa	.004		.10	
E3	.124	.132	3.15	3.35					
E4	.270	---	6.86	---					
E5	.346	.350	8.79	8.89					
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TITLE: TO-270 WIDE BODY 14 LEAD GULL WING					DOCUMENT NO: 98ASA10653D			REV: A	
					CASE NUMBER: 1621-02			19 JUN 2007	
					STANDARD: NON-JEDEC				

PRODUCT DOCUMENTATION AND SOFTWARE

Refer to the following documents and software to aid your design process.

Application Notes

- AN1907: Solder Reflow Attach Method for High Power RF Devices in Over-Molded Plastic Packages
- AN1955: Thermal Measurement Methodology of RF Power Amplifiers
- AN1977: Quiescent Current Thermal Tracking Circuit in the RF Integrated Circuit Family
- AN1987: Quiescent Current Control for the RF Integrated Circuit Device Family
- AN3263: Bolt Down Mounting Method for High Power RF Transistors and RFICs in Over-Molded Plastic Packages
- AN3789: Clamping of High Power RF Transistors and RFICs in Over-Molded Plastic Packages

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

Software

- Electromigration MTTF Calculator
- RF High Power Model

For Software, do a Part Number search at <http://www.freescale.com>, and select the “Part Number” link. Go to the Software & Tools tab on the part’s Product Summary page to download the respective tool.

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Oct. 2008	• Initial Release of Data Sheet
1	June 2011	• Changed ESD Human Body Model rating from Class 1C to Class 0 to reflect recent ESD test results of the device, p. 2 • Fig. 13, MTTF versus Junction Temperature removed, p. 8. Refer to the device’s MTTF Calculator available at freescale.com/RFpower. Go to Design Resources > Software and Tools. • Fig. 14, CCDF W-CDMA IQ Magnitude Clipping, Single-Carrier Test Signal and Fig. 15, Single-Carrier W-CDMA Spectrum updated to show the undistorted input test signal, p. 8 (renumbered as Fig. 13 and Fig. 14 after Fig. 13 removed) • Added AN3789, Clamping of High Power RF Transistors and RFICs in Over-Molded Plastic Packages to Product Documentation, Application Notes, p. 21 • Added Electromigration MTTF Calculator and RF High Power Model availability to Product Software, p. 21
2	Feb. 2012	• Table 3, ESD Protection Characteristics, removed the word “Minimum” after the ESD class rating. ESD ratings are characterized during new product development but are not 100% tested during production. ESD ratings provided in the data sheet are intended to be used as a guideline when handling ESD sensitive devices, p. 2 • Corrected bias conditions throughout the data sheet to reflect the true testing methodology. Changed $I_{DQ1A} = I_{DQ1B} = 190 \text{ mA}$ to $I_{DQ1A} + I_{DQ1B} = 190 \text{ mA}$ and changed $I_{DQ2A} = I_{DQ2B} = 925 \text{ mA}$ to $I_{DQ2A} + I_{DQ2B} = 925 \text{ mA}$. • Removed Fig. 5, Possible Circuit Topologies, and renumbered all subsequent figures, p. 5-10

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